

REMARKS

Claims 1 and 5 were rejected under 35 U.S.C. § 102(b) as anticipated by U.S. Patent No. 5,532,853 to Song et al. Claims 2-4, 6 and 7 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Song et al. Claim 8 was rejected under 35 U.S.C. § 103(a) as being unpatentable over Song et al. in view of the Related Art.

The Examiner considered Song et al. as disclosing an organic semiconductor element including an organic semiconductor layer 404, a gate insulation 402, a gate electrode 301D, a source electrode 303 and a drain electrode 302A and a gate oxide film 401 substantially as claimed, citing Fig. 12 and column 6, lines 11-55.

Applicants traverse, and respectfully request the Examiner to reconsider in view of the amendment to the claims and the following remarks.

As defined in amended claim 1, a characteristic feature of the invention lies in a gate installation layer consisting of an organic compound that improves the crystal growth of the organic semiconductor layer formed thereon. This preferred embodiment of the invention is discussed, for example, at page 7, lines 13-18 of the specification. Namely, as described therein, "the material of the gate insulation layer 4 may be a material that affords favorable crystal growth for the organic semiconductor element constituting the organic semiconductor layer 5 formed on the gate installation layer 4, it being acceptable to use an organic material that raises the orientation of the semiconductor crystals, or the like, for example."

However, as discussed at page 2, lines 19-21 of the specification, organic materials generally have a low insulation strength. Thus, a gate oxide film is provided between the gate electrode and gate insulation layer so as to improve insulation strength.

On the other hand, Song et al. at column 6, lines 36 to 38 states "an insulating layer 402 such as silicon nitride (SiN_x) is formed on the oxide film 401". Thus, Song et al. does not disclose and therefore does not teach a gate insulation layer consisting of an organic compound for improving the crystal growth of the organic semiconductor layer formed thereon as required by the amended claims. This aspect of the invention also is not taught by the "Related Art."

Withdrawn method claim 9 has been amended to include all of the limitations of product claim 1. Upon allowance of product claim 1, and as a matter of right, the Examiner is respectfully requested to rejoin withdrawn method claims 9-14 pursuant to MPEP §821.04.

For the above reasons, it is respectfully submitted that the amended claims are neither anticipated nor obvious over Song et al., alone, or in view of the "Related Art", and withdrawal of the foregoing rejections is respectfully requested.

Withdrawal of all rejections and allowance of claims 1-14 is earnestly solicited.

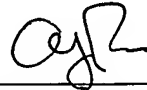
In the event that the Examiner believes that it may be helpful to advance the prosecution of this application, the Examiner is invited to contact the undersigned at the local Washington, D.C. telephone number indicated below.

AMENDMENT UNDER 37 C.F.R. § 1.114(c)
U.S. Application No.: 10/765,220

Q79569

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,



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